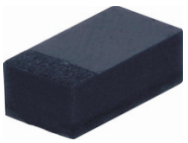
SMD Schottky Barrier Diode

COMCHIP
SMD Diodes Specialist

CDBERT0230R(RoHS Device)

Io = 200 mA
V_R = 30 Volts



Features

- Low reverse current.
- Designed for mounting on small surface.
- Extremely thin / leadless package.
- Majority carrier conduction.

Mechanical data

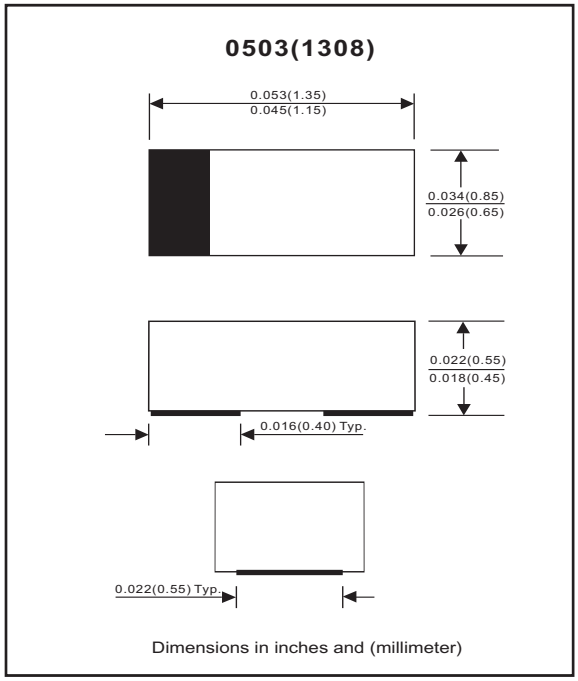
Case: 0503(1308) standard package, molded plastic.

Terminals: Gold plated, solderable per MIL-STD-750,method 2026.

Marking code: cathode band & BB

Mounting position: Any

Weight: 0.0011 gram(approx.).



Maximum Rating (at T_A=25°C unless otherwise noted)

Parameter	Conditions	Symbol	Min	Typ	Max	Unit
Repetitive peak reverse voltage		V_{RRM}			35	V
Reverse voltage		V_R			30	V
Average forward current		I_O			200	mA
Forward current,surge peak	8.3ms single half sine-wave superimposed on rate load(JEDEC method)	I_{FSM}			1	A
Storage temperature		T_{STG}	-40		+125	°C
Junction temperature		T_j			+125	°C

Electrical Characteristics (at T_A=25°C unless otherwise noted)

Parameter	Conditions	Symbol	Min	Typ	Max	Unit
Forward voltage	I_F = 200 mA	V_F			0.6	V
Reverse current	V_R = 10 V	I_R			1	uA

RATING AND CHARACTERISTIC CURVES (CDBERT0230R)

Fig. 1 - Forward characteristics

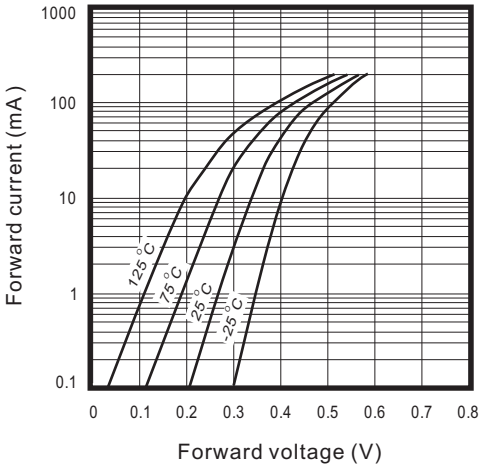


Fig. 2 - Reverse characteristics

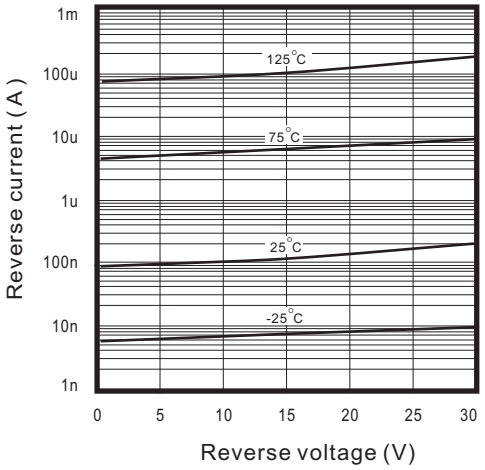


Fig. 3 - Capacitance between terminals characteristics

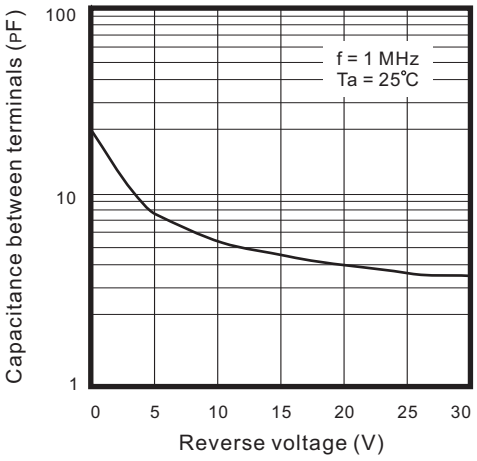


Fig.4 - Current derating curve

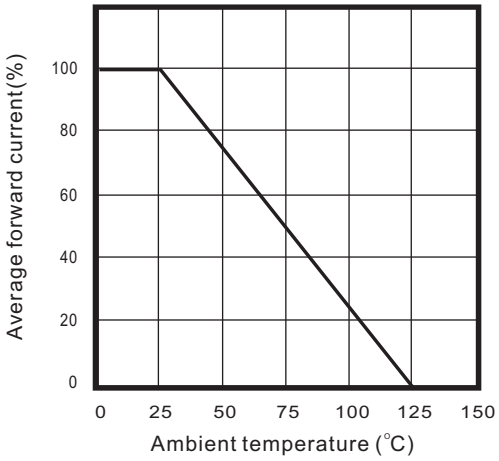


Fig. 5 - VF Dispersion map

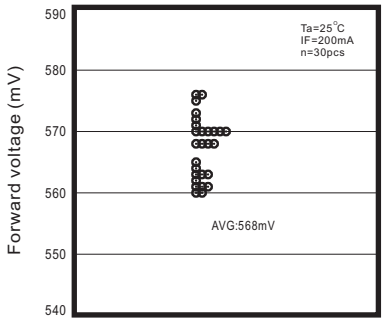


Fig. 6 - IR Dispersion map

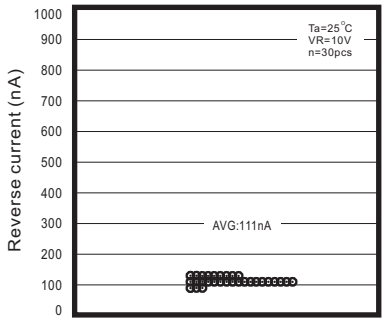


Fig. 7 - CT Dispersion map